V_{RRM}	1800	V
$I_{T(AV)}$(@ T_C = 85)	90	A
I_{TSM}(@ t_P = 10ms)	1800	A
V_T(Max)	1.80	V

Half-bridge SCR configuration integrated in a single package

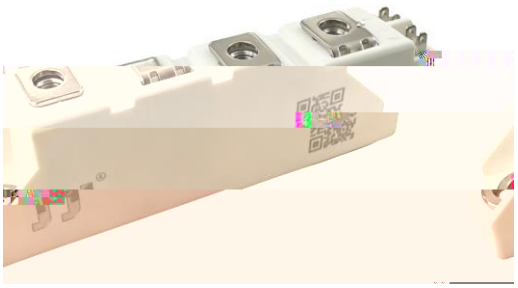
High-thermal-conductivity DBC insulation for excellent heat dissipation

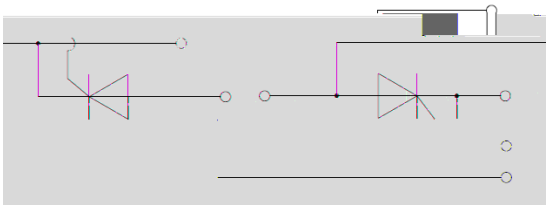
Vacuum soldering technology for enhanced reliability

Heating control

Light control system

DC motor



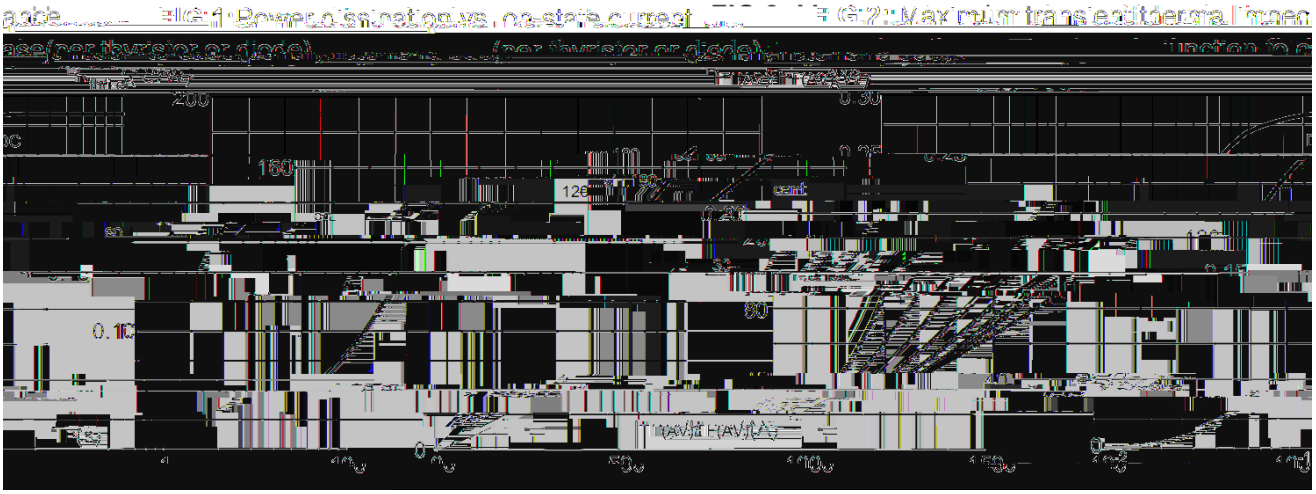


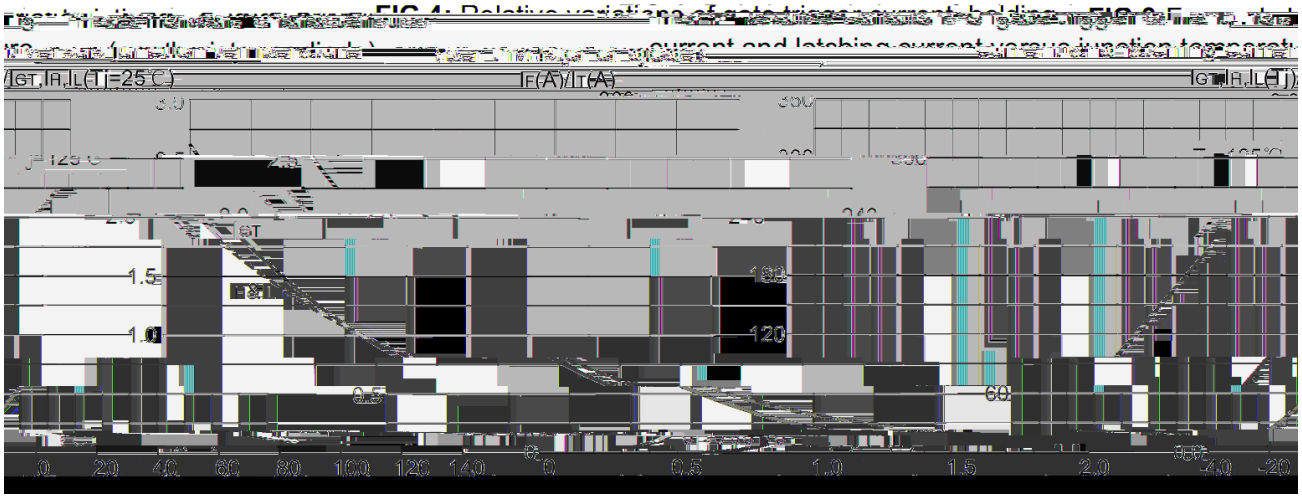
(@ T_C = 25℃ unless otherwise specified)

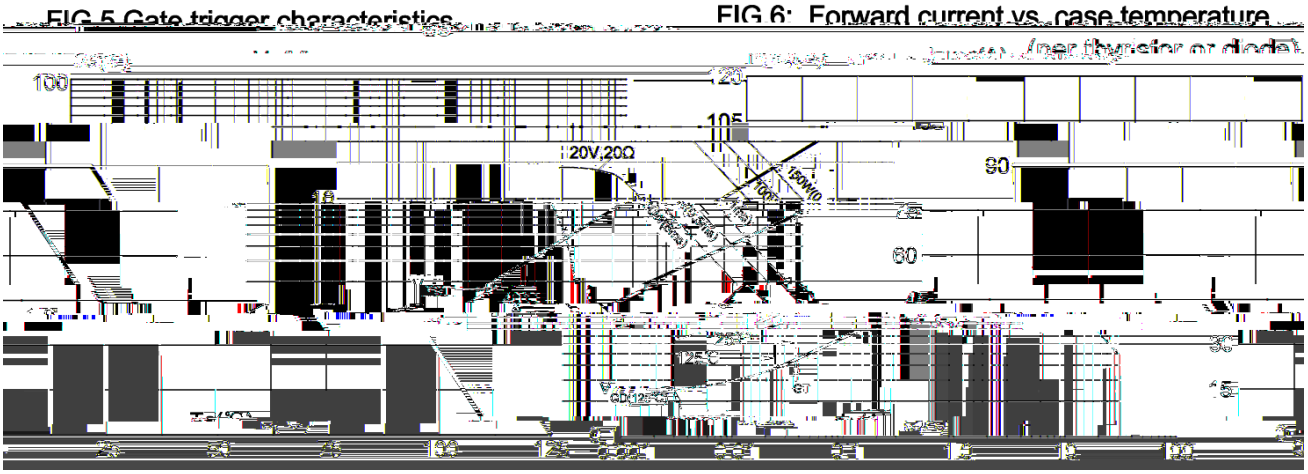
Repetitive peak off-state voltage	Tvj = 25℃	V_{DRM}	1800	V
Repetitive peak reverse voltage	Tvj = 25℃	V_{RRM}	1800	V
Non-repetitive peak off-state voltage	Tvj = 25℃	V_{DSM}	1900	V
Non-repetitive peak reverse voltage	Tvj = 25℃	V_{RSM}	1900	V
Average forward current	T_C = 85℃	$I_{T(AV)}$	90	A
Forward surge current	1/2 cycle, Sine wave, 50Hz Tvj = 25	I_{TSM}	1800	A
I^2t value for fusing		I^2t	16200	A^2s
Critical rate of rise of on-state current	I_G=2×I_{GT}	di/dt	150	A/ s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +125	
Storage temperature range		T_{stg}	-40 ~ +125	

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JMT90KB18T1A	JMT90KB18T1A	T1A	100±5g/PCS	10 PCS	120 PCS







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